ΡΛΝ	ĴΪΤ
	SEMI CONDUCTOR

100V N-Channel Enhancement Mode MOSFET

Current

Voltage

13A

Features

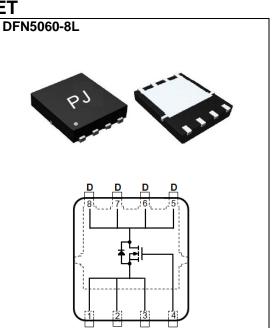
• RDS(ON), VGS@10V, ID@6.5A<115mΩ

100 V

- RDS(ON), VGS@4.5V, ID@4A<120mΩ ٠
- Advanced Trench Process Technology ٠
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive .
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026 •
- Approx. Weight: 0.0028 ounces, 0.08 grams •
- Marking: Q5472A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAME	ſER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V
Continuous Drain Current	T _C =25°C		13	
	T _C =100°C	ID	8	А
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	52	
Power Dissipation	T _C =25°C		41	
	T _C =100°C	PD	16	W
Continuous Drain Current	T _A =25°C		2.9	А
	T _A =70°C	I _D	2.3	A
Power Dissipation	T _A =25°C	2	2.0	
	T _A =70°C	PD	1.3	W
Single Pulse Avalanche Energy	(Note 6)	E _{AS}	6.1	mJ
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	3.05	9 0 (M)
	Junction to Ambient	R _{θJA}	62.5	°C/W

Maximum Junction Temperature ted only By

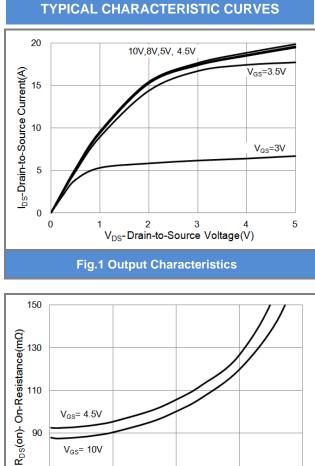


Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.76	2.5	V
Drain-Source On-State Resistance		V _{GS} =10V,I _D =6.5A	-	92	115	mΩ
	R _{DS(on)}	V _{GS} =4.5V,I _D =4A	-	95	120	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V_{DS} =50V, I_{D} =2A, V_{GS} =10V ^(Note 1,2)	-	20	-	nC
Gate-Source Charge	Q _{gs}		-	3.2	-	
Gate-Drain Charge	Q _{gd}		-	3.6	-	
Input Capacitance	Ciss	· V _{DS} =25V, V _{GS} =0V, · f=1.0MHZ	-	1413	-	pF
Output Capacitance	Coss		-	60	-	
Reverse Transfer Capacitance	Crss		-	34	-	
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =1A, V_{GS} =10V,	-	18	-	
Turn-On Rise Time	tr		-	4.3	-	ns
Turn-Off Delay Time	td _(off)		-	41	-	
Turn-Off Fall Time	t _f	$R_{G}=3.3\Omega^{(Note 1,2)}$	-	4.2	-	
Drain-Source Diode	•		•	•	•	
Maximum Continuous Drain-Source					40	•
Diode Forward Current	I _S		-	-	13	A
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.73	1	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{®JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =11A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.



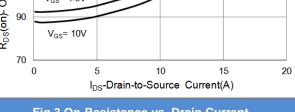
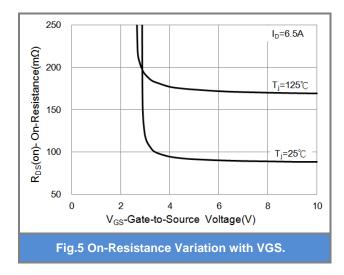
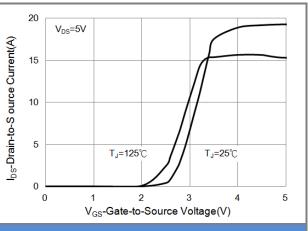


Fig.3 On-Resistance vs. Drain Current







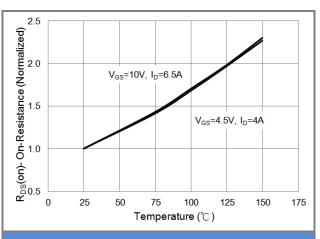
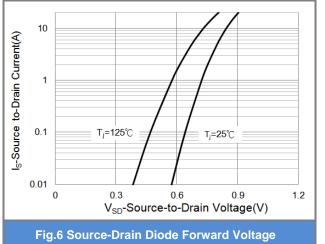
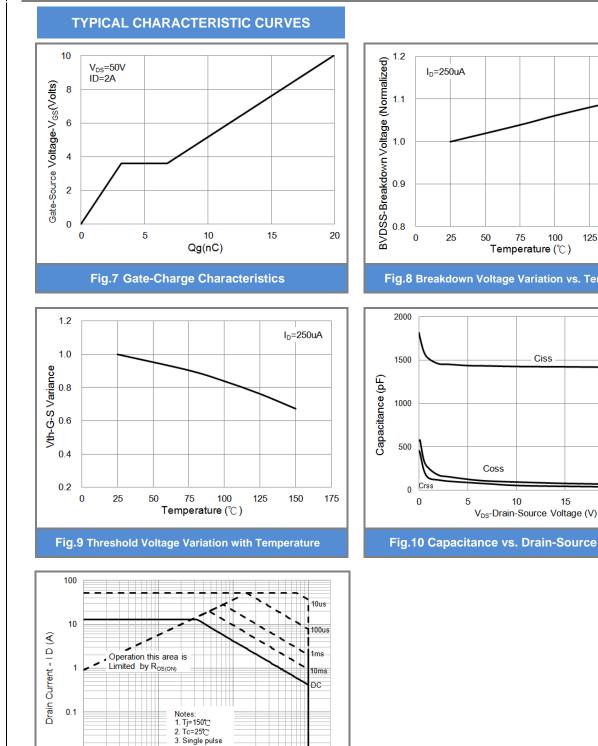


Fig.4 On-Resistance vs. Junction temperature



0.01 0.1



10

V_{DS}-Drain-Source Voltage (V) Fig.11 Maximum Safe Operating Area

1

100

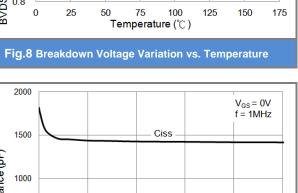
PJQ5472A



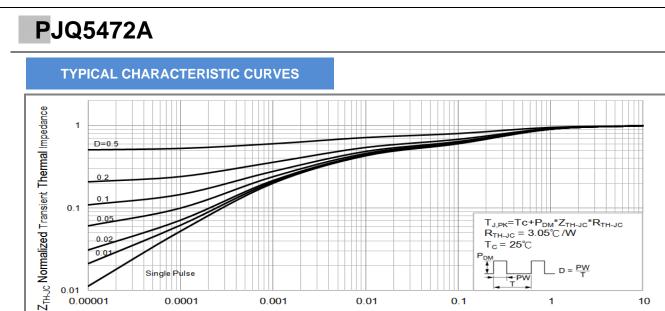


15 20 25

Fig.10 Capacitance vs. Drain-Source Voltage



July 21,2015-REV.00



t, Pulse Width (Sec)

Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





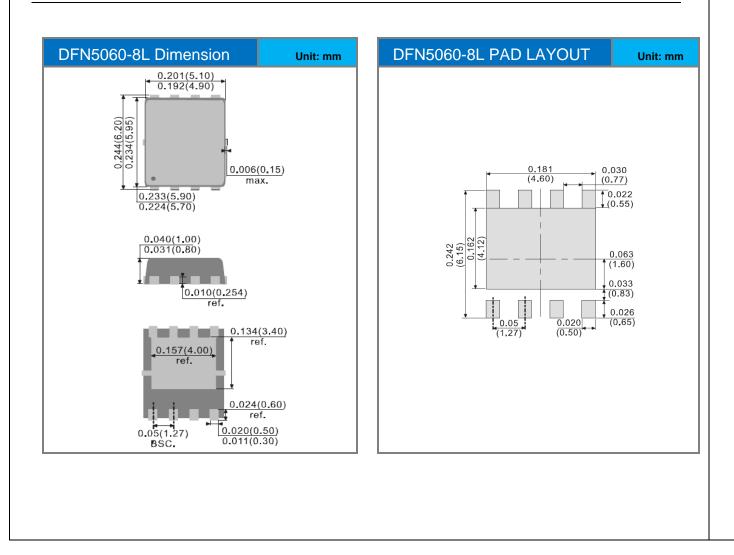




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5472A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5472A	Halogen free

Packaging Information & Mounting Pad Layout





Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.